

In the disclosure:

Please change the paragraph at page 1, line 21, as follows:

--As the following consideration shows, such a thin SiO₂ intermediate layer reduces the dielectric effectiveness of the substitute material. If we assume that the thickness $\underline{t_{high-k}}$ of the alternative dielectric is to afford the same capacitance as an SiO₂ layer of the equivalent thickness t_{eq} , that gives:

$$\underline{t_{high-k}} = (k_{high-k} / k_{SiO_2}) t_{eq}, \quad (1)$$

wherein k_{SiO_2} is the dielectric constant of the SiO₂. As the SiO₂ intermediate layer represents a second capacitance C_{SiO_2} connected in series with the alternative dielectric, the resulting capacitance can be calculated as follow:

$$1/C_{res} = 1/C_{high-k} + 1/C_{SiO_2}, \quad (2)$$

wherein C_{high-k} is the capacitance of the dielectric layer. Using (1), that then gives the following for the equivalent thickness of the layer system t_{eq}^s , comprising a thin SiO₂ layer t_{SiO_2} and the dielectric layer $\underline{t_{high-k}}$,

$$t_{eq}^s = t_{SiO_2} + (k_{SiO_2} / k_{high-k}) \underline{t_{high-k}}. \quad (3)--$$